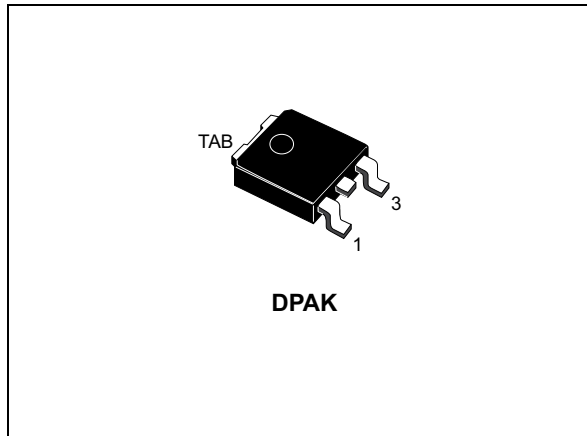


## Automotive-grade N-channel 500 V, 0.28 $\Omega$ typ., 12 A MDmesh™ II Power MOSFET in a DPAK package

Datasheet - production data



### Features

Order code	$V_{DS} @ T_{Jmax}$	$R_{DS(on) max}$	$I_D$
STD14NM50N	550 V	0.32 $\Omega$	12 A

- Designed for automotive applications and AEC-Q101 qualified
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

### Applications

- Switching applications

### Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Figure 1. Internal schematic diagram

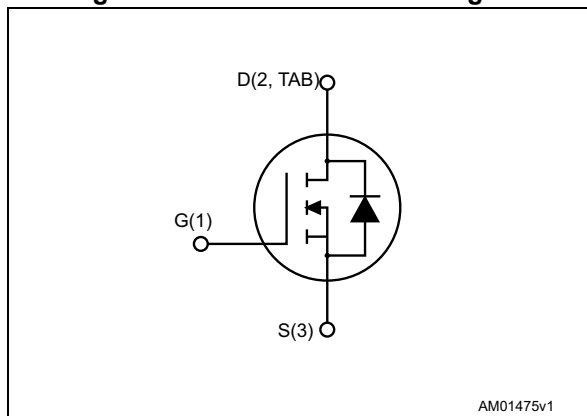


Table 1. Device summary

Order code	Marking	Package	Packaging
STD14NM50N	14NM50N	DPAK	Tape and reel

# Contents

- 1      Electrical ratings ..... 3**
- 2      Electrical characteristics ..... 4**
  - 2.1    Electrical characteristics (curves) ..... 6
- 3      Test circuits ..... 8**
- 4      Package information ..... 9**
  - 4.1    DPAK package information ..... 10
- 5      Packing mechanical data ..... 13**
- 6      Revision history ..... 15**

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	500	V
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	12	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	8	A
$I_{DM}^{(1)}$	Drain current (pulsed)	48	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	90	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$T_{stg}$	Storage temperature	- 55 to 150	$^\circ\text{C}$
$T_j$	Max. operating junction temperature	150	$^\circ\text{C}$

1. Pulse width limited by safe operating area.
2.  $I_{SD} \leq 12\text{ A}$ ,  $di/dt \leq 400\text{ A/s}$ ,  $V_{DS\text{ peak}} \leq V_{(BR)DSS}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$ .

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.39	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	50	$^\circ\text{C/W}$

1. When mounted on 1inch<sup>2</sup> FR-4 board, 2 oz Cu.

**Table 4. Avalanche data**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ max)	4	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	172	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified).

**Table 5. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 1\text{ mA}$	500			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 500\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0, V_{DS} = 500\text{ V}, T_C = 125\text{ °C}$			100	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 25\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 6\text{ A}$		0.28	0.32	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{GS} = 0, V_{DS} = 50\text{ V}, f = 1\text{ MHz}$	-	816	-	pF
$C_{oss}$	Output capacitance		-	60	-	pF
$C_{rss}$	Reverse transfer capacitance		-	3	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0\text{ to }50\text{ V}$	-	157	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz open drain}$	-	4.5	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 400\text{ V}, I_D = 12\text{ A}, V_{GS} = 10\text{ V}$ (see <a href="#">Figure 13</a> )	-	27	-	nC
$Q_{gs}$	Gate-source charge		-	5	-	nC
$Q_{gd}$	Gate-drain charge		-	15	-	nC

1.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DS}$

**Table 7. Switching times**

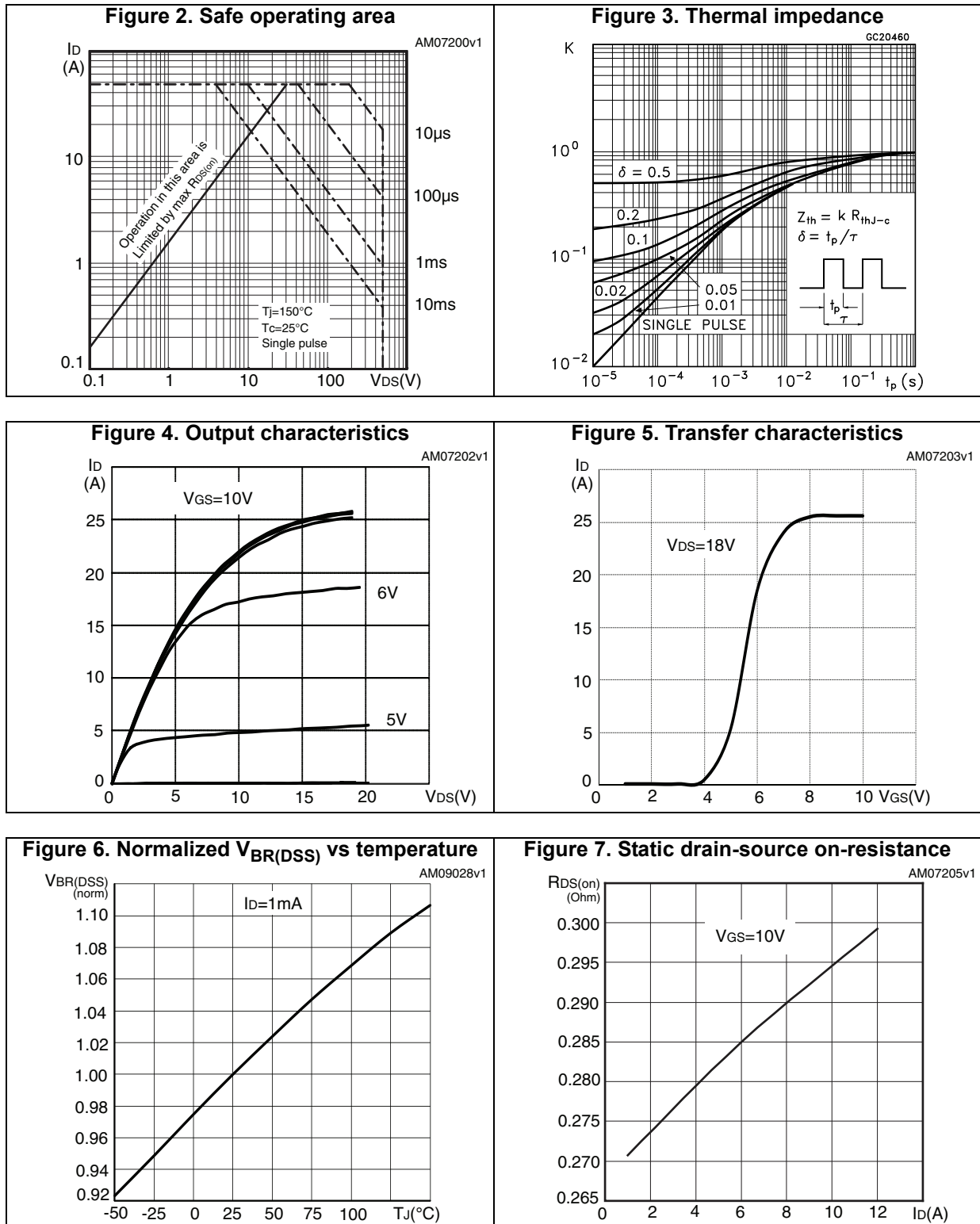
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$ , $I_D = 12\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 13</a> )	-	12	-	ns
$t_r$	Rise time		-	16	-	ns
$t_{d(off)}$	Turn-off-delay time		-	42	-	ns
$t_f$	Fall time		-	22	-	ns

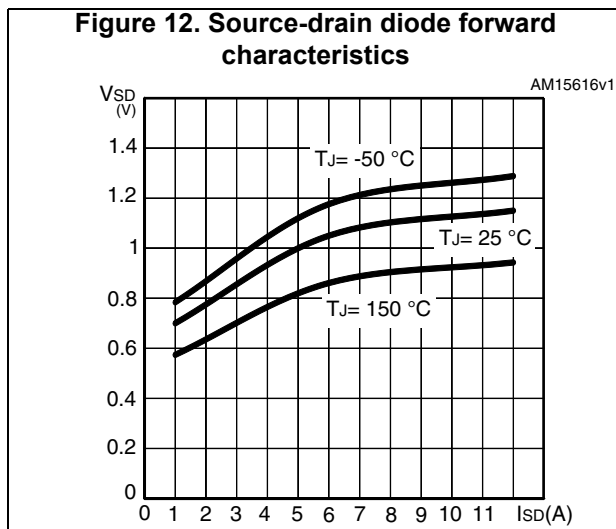
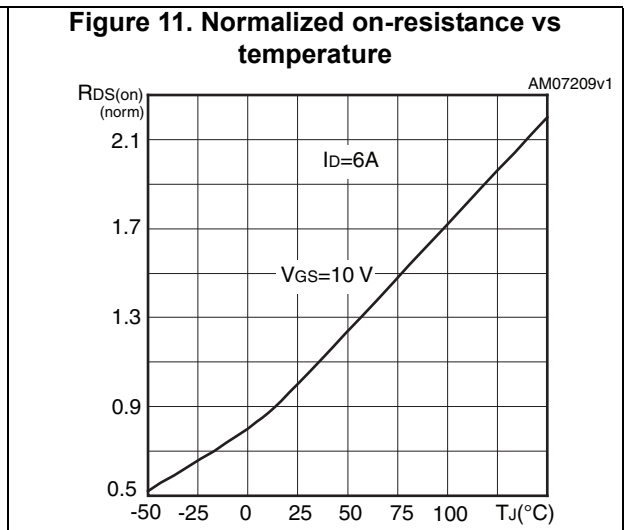
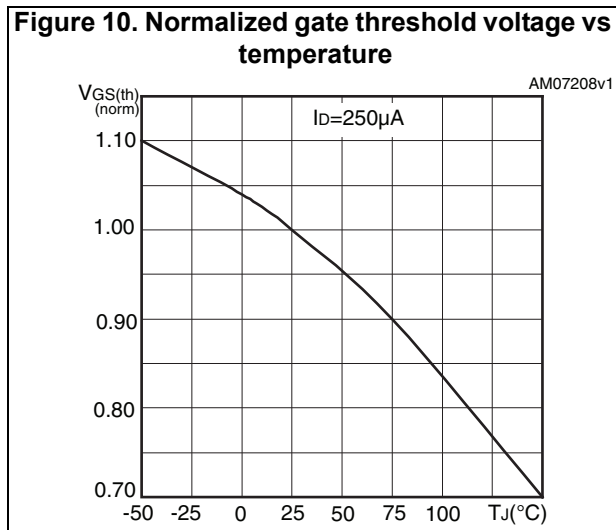
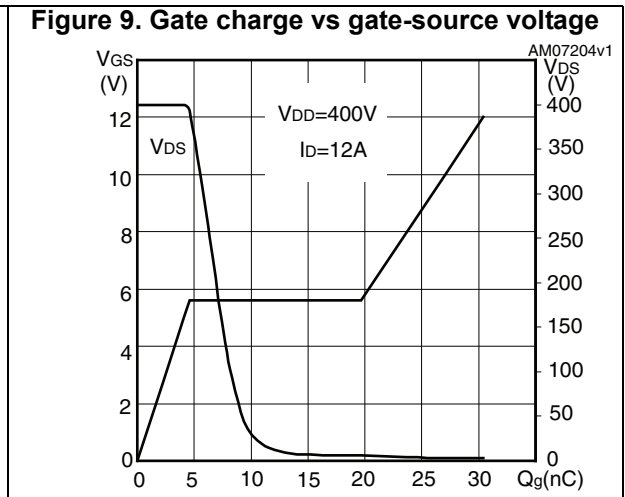
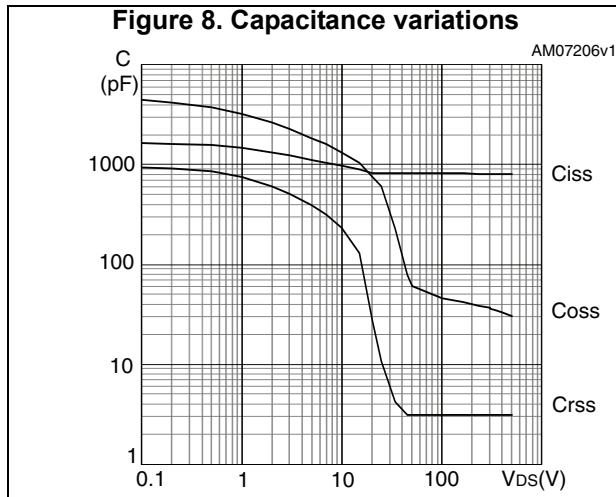
**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		12	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		48	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0$ , $I_{SD} = 12\text{ A}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 12\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see <a href="#">Figure 17</a> )	-	252		ns
$Q_{rr}$	Reverse recovery charge		-	2.8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	22		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 12\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 17</a> )	-	300		ns
$Q_{rr}$	Reverse recovery charge		-	3.3		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	22.2		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

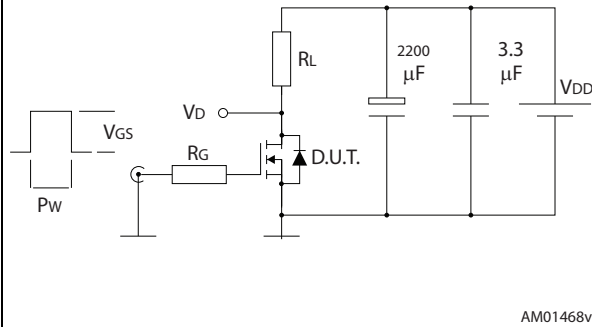
## 2.1 Electrical characteristics (curves)





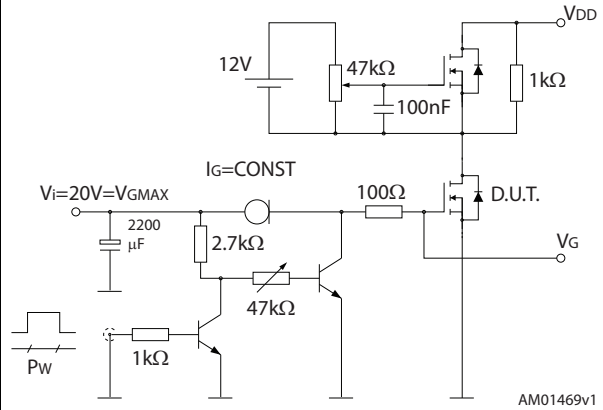
### 3 Test circuits

**Figure 13. Switching times test circuit for resistive load**



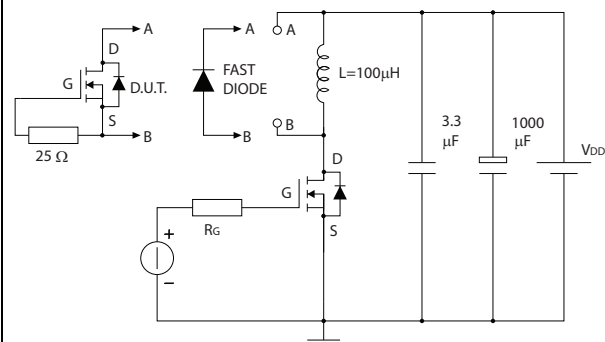
AM01468v1

**Figure 14. Gate charge test circuit**



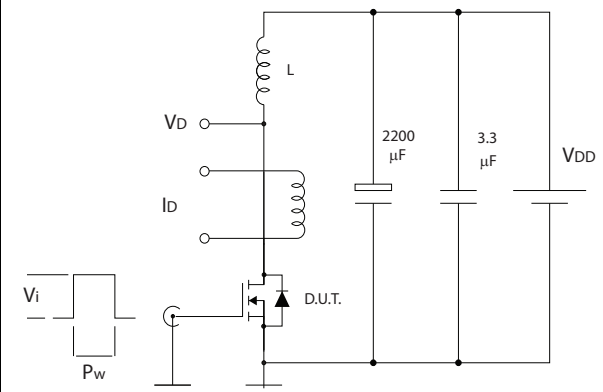
AM01469v1

**Figure 15. Test circuit for inductive load switching and diode recovery times**



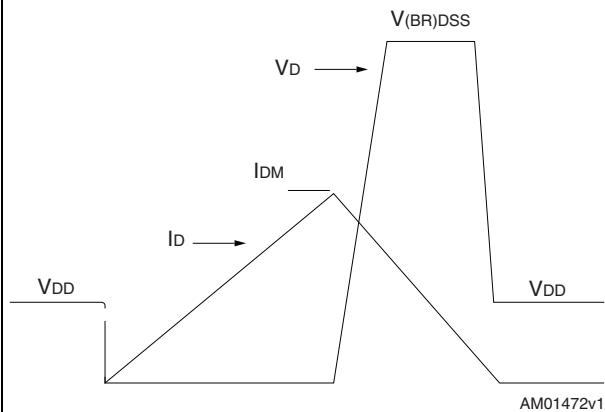
AM01470v1

**Figure 16. Unclamped inductive load test circuit**



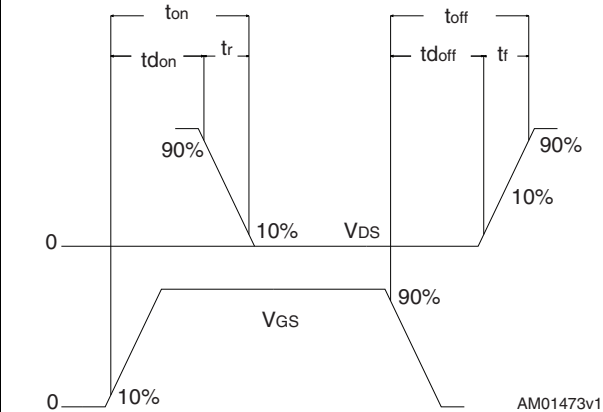
AM01471v1

**Figure 17. Unclamped inductive waveform**



AM01472v1

**Figure 18. Switching time waveform**



AM01473v1



## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

### 4.1 DPAK package information

Figure 19. DPAK (TO-252) type A2 package outline

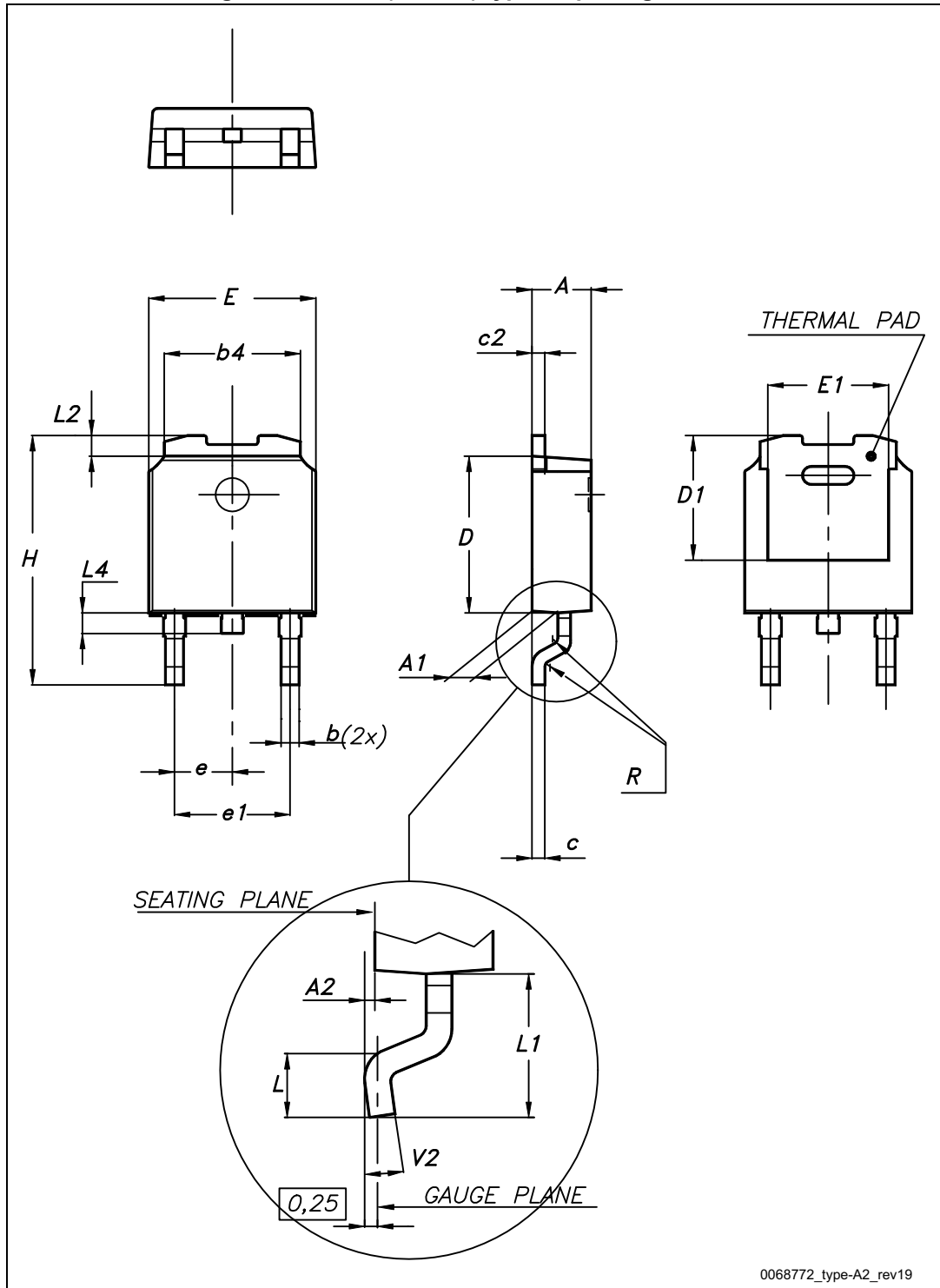
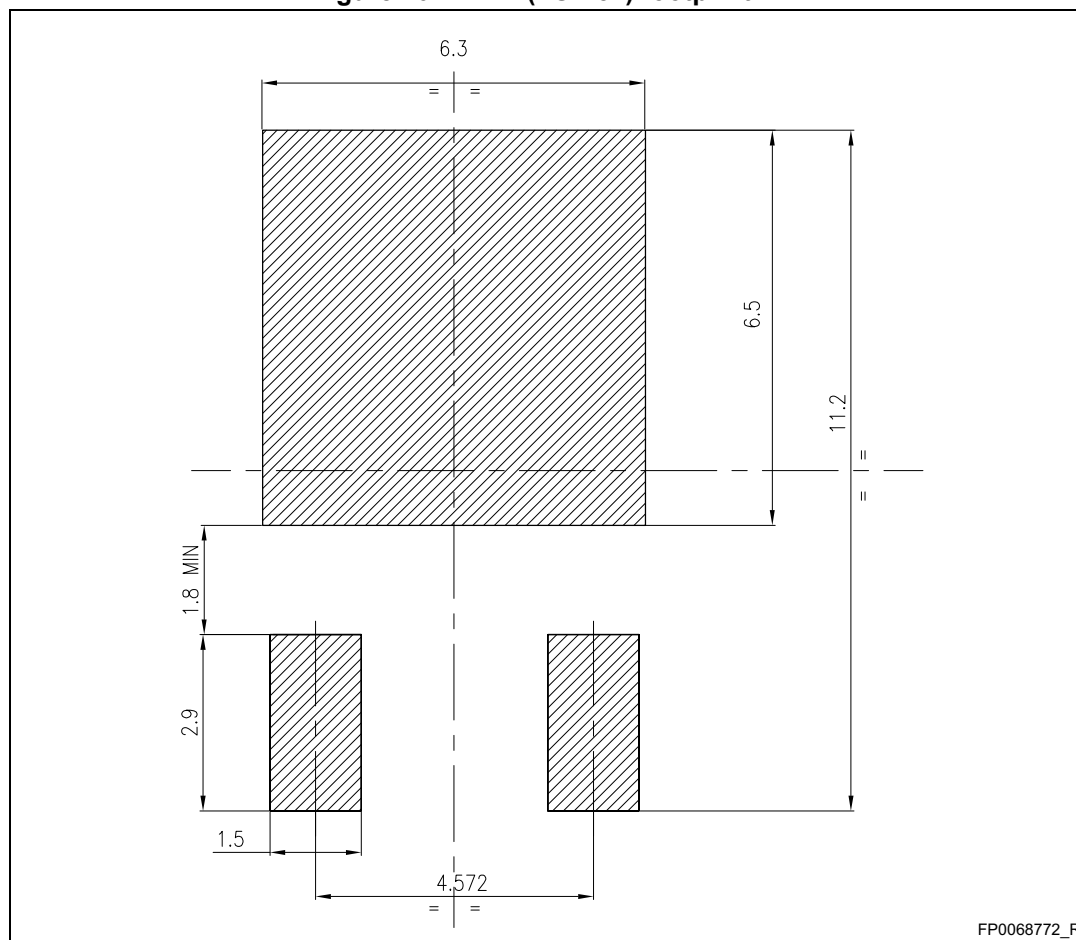


Table 9. DPAK (TO-252) type A2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 20. DPAK (TO-252) footprint (a)



a. All dimensions are in millimeters

# 5 Packing mechanical data

Figure 21. Tape

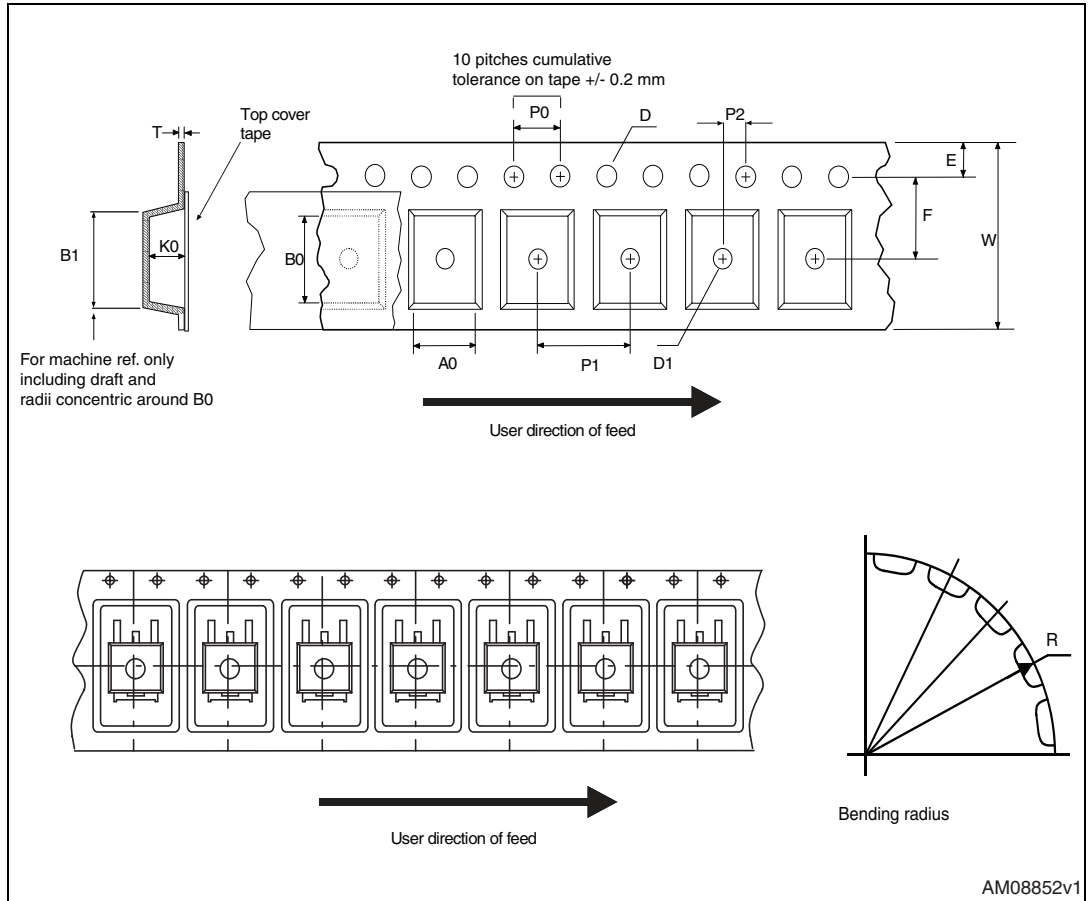


Figure 22. Reel

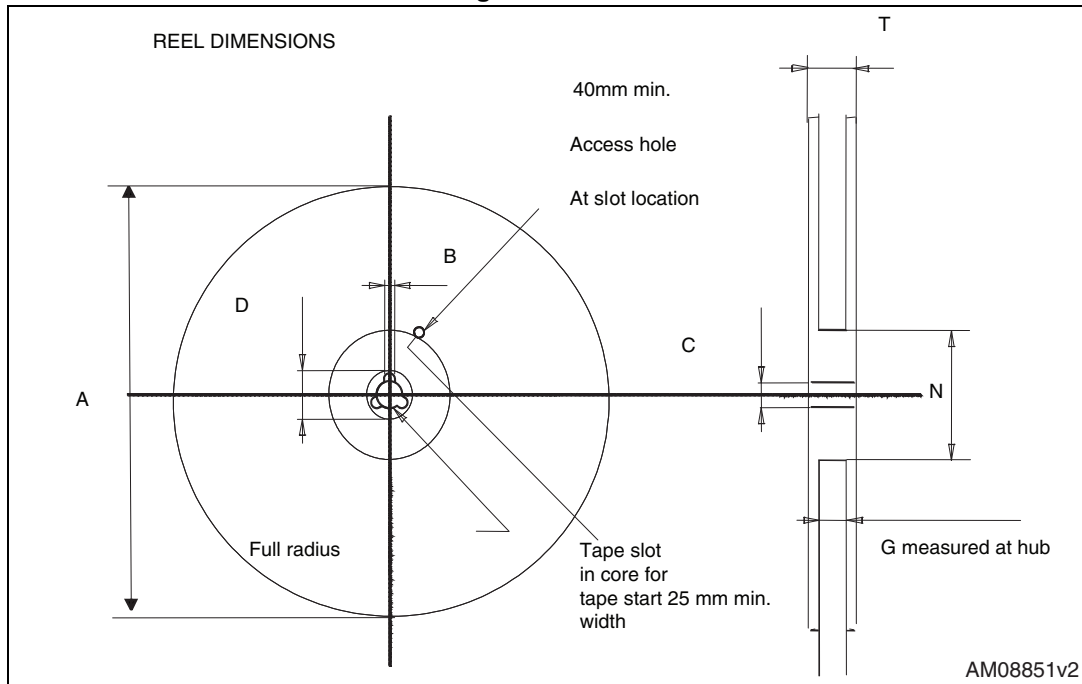


Table 10. D<sup>2</sup>PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

## 6 Revision history

Table 11. Document revision history

Date	Revision	Changes
27-Jun-2014	1	First release.
03-Sep-2015	2	Updated <i>DPAK package information</i> . Minor text changes.
09-Sep-2015	3	Updated figure and table MD for DPAK package information Minor text changes.

**IMPORTANT NOTICE – PLEASE READ CAREFULLY**

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2015 STMicroelectronics – All rights reserved



## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [STMicroelectronics](#) manufacturer:*

Other Similar products are found below :

[614233C](#) [648584F](#) [IRFD120](#) [JANTX2N5237](#) [SPP20N60S5XK](#) [FCA20N60\\_F109](#) [FDZ595PZ](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#)  
[TPCC8103,L1Q\(CM](#) [MIC4420CM-TR](#) [VN1206L](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [SSM6J414TU,LF\(T](#) [751625C](#)  
[BUK954R8-60E](#) [DMN3404LQ-7](#) [NTE6400](#) [SQJ402EP-T1-GE3](#) [2SK2614\(TE16L1,Q\)](#) [2N7002KW-FAI](#) [DMN1017UCP3-7](#)  
[EFC2J004NUZTDG](#) [ECH8691-TL-W](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE221](#) [NTE2384](#) [NTE2903](#) [NTE2941](#)  
[NTE2945](#) [NTE2946](#) [NTE2960](#) [NTE2967](#) [NTE2969](#) [NTE2976](#) [NTE455](#) [NTE6400A](#) [NTE2910](#) [NTE2916](#) [NTE2956](#) [NTE2911](#)  
[DMN2080UCB4-7](#) [TK10A80W,S4X\(S](#) [SSM6P69NU,LF](#)